



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	1.9Ω @ V _{GS} = -4.5V	-0.33A
	2.4Ω @ $V_{GS} = -2.5V$	-0.29A
	3.4Ω @ V _{GS} = -1.8V	-0.24A
	5.0Ω @ V _{GS} = -1.5V	-0.2A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General purpose interfacing switches
- Power management functions
- Analog switches

Features and Benefits

- Low Package Profile, 0.42mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, -1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

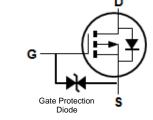
Mechanical Data

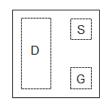
- Package: X2-DFN0606-3
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)





Bottom View





Equivalent Circuit

Top View Package Pin Configuration

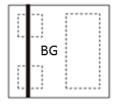
Ordering Information (Note 4)

Part Number	Packago	Packing		
Fait Number	Package	Qty.	Carrier	
DMP22D5UFZ-7B	X2-DFN0606-3	10K	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

Marking Information



Top View Bar Denotes Gate

and Source Side

BG = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	-20	V
Gate-Source Voltage	Vgss	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	lD	-0.33 -0.2	А
Pulsed Drain Current (Note 6)	IDM	-0.8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	0.32	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _θ JA	394	°C/W
Total Power Dissipation (Note 6)	Steady State	PD	0.95	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	132	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

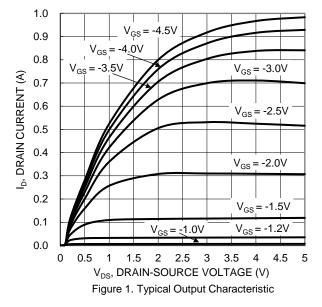
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current @Tc = +25°C	IDSS	_	_	-1	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage		_	_	±10	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	_	1.9	Ω	$V_{GS} = -4.5V, I_{D} = -100mA$
Static Drain-Source On-Resistance	D	_	_	2.4		$V_{GS} = -2.5V, I_{D} = -50mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	3.4		$V_{GS} = -1.8V, I_{D} = -20mA$
		_	_	5.0		$V_{GS} = -1.5V, I_{D} = -10mA$
Diode Forward Voltage	V _{SD}	_	_	-1.1	V	$V_{GS} = 0V$, $I_S = -10mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	17	_	pF	101/1/
Output Capacitance	Coss	_	4.1	_	pF	V _{DS} = -16V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.7	_	pF	1 - 1.011112
Total Gate Charge	Qg	_	0.3	_	nC	V 45V V 40V
Gate-Source Charge	Qgs	_	0.04	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -250$ mA
Gate-Drain Charge	Qgd	_	0.1	_	nC	- ID = -230IIIA
Turn-On Delay Time	t _D (ON)	_	7.3	_	ns	
Turn-On Rise Time	t _R		20.7	_	ns	V _{DD} = -15V, V _{GS} = -4.5V,
Turn-Off Delay Time	tD(OFF)	_	185	_	ns	$R_G = 2\Omega$, $I_D = -200$ mA
Turn-Off Fall Time	tF	_	97	_	ns	

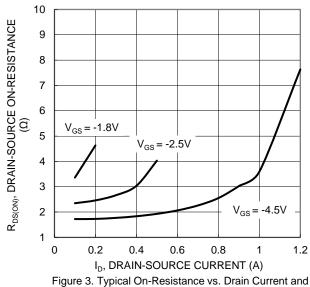
Notes:

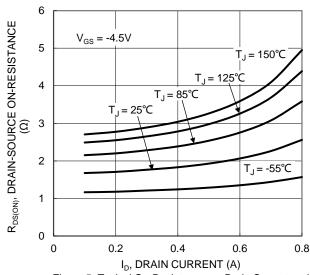
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. 10µs pulse duty cycle = 1%.
 7. Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to product testing.



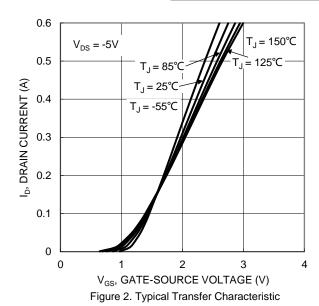


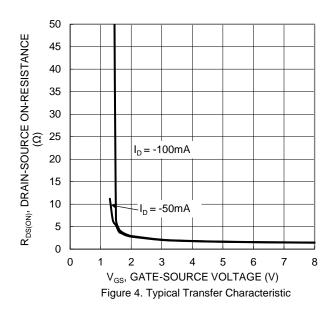




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature





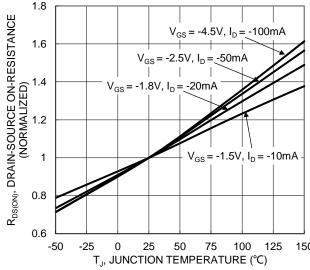


Figure 6. On-Resistance Variation with Temperature





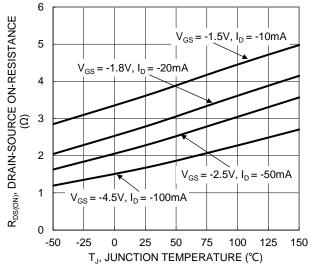
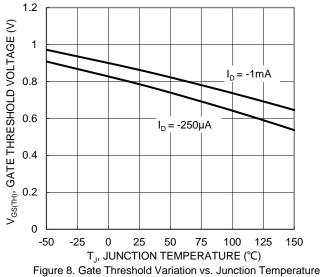


Figure 7. On-Resistance Variation with Temperature



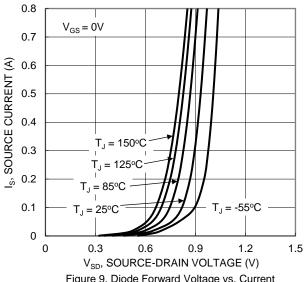
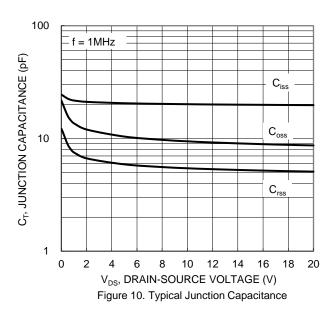


Figure 9. Diode Forward Voltage vs. Current

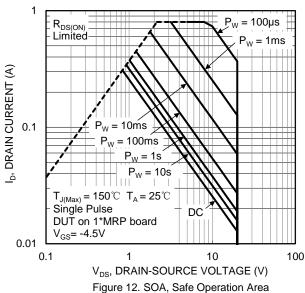
 $V_{DS} = -10V, I_{D} = -250mA$

0.1



0.25 0.3

 Q_q (nC) Figure 11. Gate Charge



0.15

0.2

0.05

4.5

3.5

 $V_{GS}(V)$ 2.5

3

2 1.5 1

0.5

0 0

4



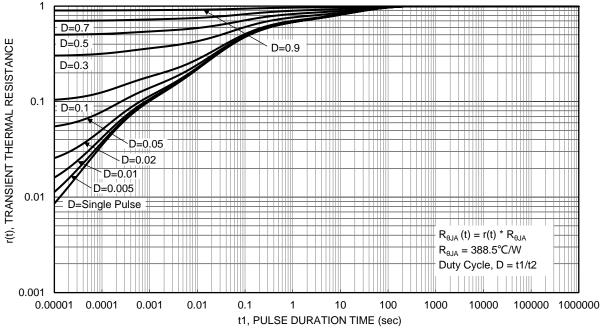


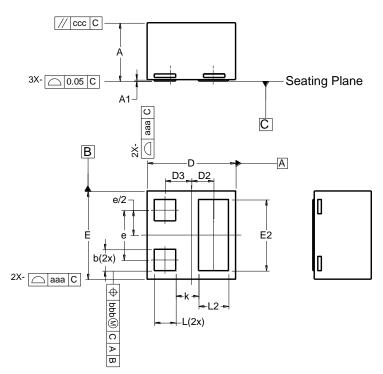
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0606-3

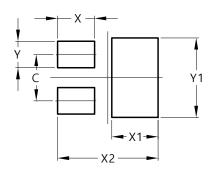


X2-DFN0606-3					
Dim	Min	Max	Тур		
Α	0.36	0.40	0.39		
A 1	0.00	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57	0.67	0.62		
D2	0.	155 BS	SC		
D3	0.	185 BS	SC		
Е	0.57	0.67	0.62		
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
L	0.10	0.20	0.15		
L2	0.11	0.31	0.21		
aaa	0.08				
bbb	0.07				
CCC	0.05				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0606-3



Dimensions	Value (in mm)
С	0.350
Х	0.280
X1	0.350
X2	0.760
Y	0.200
Y1	0.600



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